## Kazuya Masu

List of Publications by Year in descending order

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221 papers 1,925 citations

361413 20 h-index 434195 31 g-index

221 all docs

221 docs citations

times ranked

221

1006 citing authors

#	Article	IF	CITATIONS
1	Complete planarization of via holes with aluminum by selective and nonselective chemical vapor deposition. Applied Physics Letters, 1990, 57, 1221-1223.	3.3	71
2	Design of sub-1g microelectromechanical systems accelerometers. Applied Physics Letters, 2014, 104, .	3.3	64
3	Selective aluminum chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1992, 10, 856-862.	2.1	55
4	New binary sequences with zero-correlation duration for approximately synchronised CDMA. Electronics Letters, 2000, 36, 991.	1.0	54
5	A Bidirectional- and Multi-Drop-Transmission-Line Interconnect for Multipoint-to-Multipoint On-Chip Communications. IEEE Journal of Solid-State Circuits, 2008, 43, 1020-1029.	5.4	53
6	Acceptor energy level for Zn in Galâ^xAlxAs. Journal of Applied Physics, 1980, 51, 1060-1064.	2.5	48
7	Pyrolysis and Photolysis of Trimethylaluminum. Japanese Journal of Applied Physics, 1986, 25, 1236-1242.	1.5	46
8	On-Chip Variable Inductor Using Microelectromechanical Systems Technology. Japanese Journal of Applied Physics, 2003, 42, 2190-2192.	1.5	39
9	Selective deposition of aluminum from selectively excited metalorganic source by the rf plasma. Applied Physics Letters, 1990, 56, 1543-1545.	3.3	38
10	Transmission Electron Microscopic Observation of \$f AlN/{mbi alpha}mbox{-}Al_{2}O_{3}\$ Heteroepitaxial Interface with Initial-Nitriding AlN Layer. Japanese Journal of Applied Physics, 1995, 34, L760-L763.	1.5	38
11	Full duplex transmission operation of a 2.45-GHz asynchronous spread spectrum using a SAN convolver. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 1993, 40, 478-482.	3.0	33
12	Pulse electroplating of ultra-fine grained Au films with high compressive strength. Electrochemistry Communications, 2016, 67, 51-54.	4.7	33
13	Area-selective CVD of metals. Thin Solid Films, 1993, 228, 312-318.	1.8	32
14	On-Chip High-\$Q\$Variable Inductor Using Wafer-Level Chip-Scale Package Technology. IEEE Transactions on Electron Devices, 2006, 53, 2401-2406.	3.0	31
15	Alloy scattering potential inpâ€ŧype Ga1â^'xAlxAs. Journal of Applied Physics, 1983, 54, 5785-5792.	2.5	30
16	On-chip transmission line for long global interconnects. , 0, , .		30
17	RF-Powered Transceiver With an Energy- and Spectral-Efficient IF-Based Quadrature Backscattering Transmitter. IEEE Journal of Solid-State Circuits, 2015, 50, 2975-2987.	5.4	29
18	Integrated CMOS-MEMS Technology and Its Applications. ECS Transactions, 2014, 61, 21-39.	0.5	26

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19	Variable RF Inductor on Si CMOS Chip. Japanese Journal of Applied Physics, 2004, 43, 2293-2296.	1.5	24
20	Novel Sensor Structure and Its Evaluation for Integrated Complementary Metal Oxide Semiconductor Microelectromechanical Systems Accelerometer. Japanese Journal of Applied Physics, 2013, 52, 06GL04.	1.5	23
21	Area-Selective Aluminum Patterning Using Atomic Hydrogen Resist. Japanese Journal of Applied Physics, 1993, 32, 278-281.	1.5	22
22	Fabrication and evaluation of an on-chip micro-variable inductor. Microelectronic Engineering, 2003, 67-68, 582-587.	2.4	22
23	Differential transmission line interconnect for high speed and low power global wiring., 0,,.		21
24	A 0.5 V 5.96-GHz PLL With Amplitude-Regulated Current-Reuse VCO. IEEE Microwave and Wireless Components Letters, 2017, 27, 302-304.	3.2	21
25	Wide Tuning Range LC-VCO Using Variable Inductor for Reconfigurable RF Circuit. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 507-512.	0.3	21
26	Preparation of (AlxGa1â^'x)yIn1â^'yAs (0≤â‰6.5,y=0.47) lattice matched to InP substrates by molecular beam epitaxy. Journal of Applied Physics, 1982, 53, 7558-7560.	2.5	20
27	Temperature-Scaling Theory for Low-Temperature-Operated MOSFET with Deep-Submicron Channel. Japanese Journal of Applied Physics, 1988, 27, L1958-L1961.	1.5	20
28	On-die parameter extraction from path-delay measurements. , 2009, , .		20
29	AlN epitaxial growth on atomically flat initially nitrided $\hat{l}$ ±-Al2O3 wafer. Applied Surface Science, 1997, 117-118, 540-545.	6.1	19
30	Low temperature deposited Zr–B film applicable to extremely thin barrier for copper interconnect. Applied Surface Science, 2009, 256, 1222-1226.	6.1	19
31	A 1.3-2.8 GHz Wide Range CMOS LC-VCO Using Variable Inductor. , 2005, , .		18
32	Robust importance sampling for efficient SRAM yield analysis. , 2010, , .		18
33	A Single-Platform Simulation and Design Technique for CMOS-MEMS Based on a Circuit Simulator With Hardware Description Language. Journal of Microelectromechanical Systems, 2013, 22, 755-767.	2.5	18
34	A dual-axis MEMS capacitive inertial sensor with high-density proof mass. Microsystem Technologies, 2016, 22, 459-464.	2.0	18
35	Contribution of free electrons to Al CVD on a Si surface by photo-excitation. Applied Surface Science, 1994, 79-80, 237-243.	6.1	17
36	Accurate Array-Based Measurement for Subthreshold-Current of MOS Transistors. IEEE Journal of Solid-State Circuits, 2009, 44, 2977-2986.	5.4	17

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37	A 0.98 to 6.6 Hz Tunable Wideband VCO in a 180nm CMOS Technology for Reconfigurable Radio Transceiver. , 2006, , .		16
38	A Variability-Aware Adaptive Test Flow for Test Quality Improvement. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2014, 33, 1056-1066.	2.7	16
39	Reproducible diffusion of beryllium into GaAs during liquid phase epitaxial growth. Applied Physics Letters, 1980, 37, 182-184.	3.3	15
40	4 Gbps On-Chip Interconnection using Differential Transmission Line. , 2005, , .		15
41	Assessment of Testicular Corticosterone Biosynthesis in Adult Male Rats. PLoS ONE, 2015, 10, e0117795.	2.5	15
42	Epitaxial growth of A1N film by low-pressure MOCVD in gas-beam-flow reactor. Journal of Crystal Growth, 1991, 115, 643-647.	<b>1.</b> 5	14
43	Equivalent Circuit Analysis of RF-Integrated Inductors with/without Ferromagnetic Material. Japanese Journal of Applied Physics, 2003, 42, 2210-2213.	1.5	14
44	Auâ€"Cu Alloys Prepared by Pulse Electrodeposition toward Applications as Movable Micro-Components in Electronic Devices. Journal of the Electrochemical Society, 2018, 165, D58-D63.	2.9	14
45	In SituObservation of Electromigration in Cu Film Using Scanning µ-Reflection High-Energy Electron Diffraction Microscope. Japanese Journal of Applied Physics, 1991, 30, 3642-3645.	1.5	13
46	A dynamic reconfigurable RF circuit architecture. , 2005, , .		13
47	RF Passive Components Using Metal Line on Si CMOS. IEICE Transactions on Electronics, 2006, E89-C, 681-691.	0.6	13
48	Precursor design and selective aluminum CVD. Vacuum, 1995, 46, 1249-1253.	3.5	12
49	A 6.5-mW 5-Gbps On-Chip Differential Transmission Line Interconnect with a Low-Latency Asymmetric Tx in a 180nm CMOS Technology. , 2006, , .		12
50	A Low-Latency and High-Power-Efficient On-Chip LVDS Transmission Line Interconnect for an RC Interconnect Alternative. , 2007, , .		12
51	An Adaptive Test for Parametric Faults Based on Statistical Timing Information., 2009,,.		12
52	13.8 A 5.8GHz RF-powered transceiver with a 113& $\#$ x03BC; $W$ 32-QAM transmitter employing the IF-based quadrature backscattering technique., 2015, , .		12
53	Structure stability of high aspect ratio Ti/Au two-layer cantilevers for applications in MEMS accelerometers. Microelectronic Engineering, 2016, 159, 90-93.	2.4	12
54	Design of CMOS inverter-based output buffers adapting the cherry-hooper broadbanding technique. , 2009, , .		11

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55	SMAFTI packaging technology for new interconnect hierarchy. , 2009, , .		11
56	An arrayed accelerometer device of a wide range of detection for integrated CMOS–MEMS technology. Japanese Journal of Applied Physics, 2014, 53, 027202.	1.5	11
57	Enhancement of mechanical strength in Au films electroplated with supercritical carbon dioxide. Electrochemistry Communications, 2016, 72, 126-130.	4.7	11
58	Tensile tests of micro-specimens composed of electroplated gold. Microelectronic Engineering, 2017, 174, 6-10.	2.4	11
59	(Invited) CMOS-MEMS Based Microgravity Sensor and Its Application. ECS Transactions, 2020, 97, 91-108.	0.5	11
60	The Role of Be in  ( GaAl ) As / GaAs Solar Cells. Journal of the Electrochemical Society,	, 1 <b>29§</b> 2, 12	29,1 <b>b</b> 623-162
61	Diffusion of beryllium into GaAs during liquid phase epitaxial growth ofpâ€Ga0.2Al0.8As. Journal of Applied Physics, 1983, 54, 1574-1578.	2.5	10
62	Superiority of DMAH to DMEAA for al CVD technology. Materials Science in Semiconductor Processing, 1999, 2, 303-308.	4.0	10
63	Path clustering for adaptive test. , 2010, , .		10
64	Promoted bending strength in micro-cantilevers composed of nanograined gold toward MEMS applications. Microelectronic Engineering, 2018, 196, 20-24.	2.4	10
65	Silicon Nitride Films with Low Hydrogen Content, Low Stress, Low Damage and Stoichiometric Composition by Photo-Assisted Plasma CVD. Japanese Journal of Applied Physics, 1989, 28, L2316-L2319.	1.5	9
66	Atomic hydrogen resist process with electron beam lithography for selective Al patterning. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3270.	1.6	9
67	Reconfigurable RF circuit design for multi-band wireless chip. , 0, , .		9
68	RF Attenuation Characteristics forIn VivoWireless Healthcare Chip. Japanese Journal of Applied Physics, 2005, 44, 5275-5277.	1.5	9
69	A sub-1mw 5.5-GHz PLL with digitally-calibrated ILFD and linearized varactor for low supply voltage operation. , 2013, , .		9
70	A 0.52-V 5.7-GHz low noise sub-sampling PLL with dynamic threshold MOSFET. , 2014, , .		9
71	A 0.1 G-to-20 G integrated MEMS inertial sensor. Japanese Journal of Applied Physics, 2015, 54, 087202.	1.5	9
72	High-Strength Electroplated Au–Cu Alloys as Micro-Components in MEMS Devices. Journal of the Electrochemical Society, 2017, 164, D244-D247.	2.9	9

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73	Distributed Sensing Via Inductively Coupled Single-Transistor Chaotic Oscillators: A New Approach and Its Experimental Proof-of-Concept. IEEE Access, 2020, 8, 36536-36555.	4.2	9
74	In VivoBatteryless Wireless Communication System for Bio-MEMS Sensors. Japanese Journal of Applied Physics, 2005, 44, 2879-2882.	1.5	8
75	Physical Modeling of MEMS Variable Inductor. IEEE Transactions on Circuits and Systems II: Express Briefs, 2008, 55, 419-422.	3.0	8
76	An over-12-Gbps on-chip transmission line interconnect with a pre-emphasis technique in 90 nm CMOS. , 2008, , .		8
77	A 1.7-GHz 1.5-mW digitally-controlled FBAR oscillator with 0.03-ppb resolution. , 2008, , .		8
78	Characterization of On-Chip Multiport Inductors for Small-Area RF Circuits. IEEE Transactions on Circuits and Systems I: Regular Papers, 2009, 56, 1590-1597.	5.4	8
79	A Novel Direct Injection-Locked QPSK Modulator Based on Ring VCO in 180 nm CMOS. IEEE Microwave and Wireless Components Letters, 2014, 24, 269-271.	3.2	8
80	Sample size effect on micro-mechanical properties of gold electroplated with dense carbon dioxide. Surface and Coatings Technology, 2018, 350, 1065-1070.	4.8	8
81	Layout-Aware Compact Model of MOSFET Characteristics Variations Induced by STI Stress. IEICE Transactions on Electronics, 2008, E91-C, 1142-1150.	0.6	8
82	S-Parameter-Based Modal Decomposition of Multiconductor Transmission Lines and Its Application to De-Embedding. , 2009, , .		7
83	A capacitive CMOS–MEMS sensor designed by multi-physics simulation for integrated CMOS–MEMS technology. Japanese Journal of Applied Physics, 2014, 53, 04EE15.	1.5	7
84	Planarized Deposition of High-Quality Silicon Dioxide Film by Photoassisted Plasma CVD at 300°C Using Tetraethyl Orthosilicate. Japanese Journal of Applied Physics, 1990, 29, L2341-L2344.	1.5	6
85	Silicon dioxide film deposited by photoassisted microwave plasma CVD using TEOS. Applied Surface Science, 1994, 79-80, 327-331.	6.1	6
86	Inductance-Tuned LC-VCO for Reconfigurable RF Circuit Design. IEICE Electronics Express, 2004, $1$ , $156-159$ .	0.8	6
87	Physical design challenges to nano-CMOS circuits. IEICE Electronics Express, 2009, 6, 703-720.	0.8	6
88	Brittle Fracture of Electrodeposited Gold Observed by Micro-Compression. Materials Transactions, 2016, 57, 1257-1260.	1.2	6
89	A —244-dB FOM High-Frequency Piezoelectric Resonator-Based Cascaded Fractional-N PLL With Sub-ppb-Order Channel-Adjusting Technique. IEEE Journal of Solid-State Circuits, 2017, 52, 1123-1133.	5.4	6
90	Nanoscale Hierarchical Structure of Twins in Nanograins Embedded with Twins and the Strengthening Effect. Metals, 2019, 9, 987.	2.3	6

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91	Planar Solenoidal Inductor in Radio Frequency Micro-Electro-Mechanical Systems Technology for Variable Inductor with Wide Tunable Range and High Quality Factor. Japanese Journal of Applied Physics, 2012, 51, 05EE02.	1.5	6
92	Single Crystallization of Aluminum on SiO2by Thermal Annealing and Observation with Scanning $\hat{A}\mu$ -RHEED Microscope. Japanese Journal of Applied Physics, 1991, 30, L56-L59.	1.5	5
93	Reliability of Single Electron Transistor Circuits Based onEb/NO-Bit Error Rate Characteristics. Japanese Journal of Applied Physics, 1999, 38, 403-405.	1.5	5
94	A MOS Transistor-Array for Accurate Measurement of Subthreshold Leakage Variation. , 2007, , .		5
95	An 8.9mW 25Gb/s inductorless 1:4 DEMUX in 90nm CMOS. , 2009, , .		5
96	Radio Frequency Micro Electro Mechanical Systems Inductor Configurations for Achieving Large Inductance Variations and HighQ-factors. Japanese Journal of Applied Physics, 2010, 49, 05FG02.	1.5	5
97	An 8 channel, 20 V output CMOS switching driver with 3.3 V power supply using triple-well biasing techniques for integrated MEMS device control. Japanese Journal of Applied Physics, 2014, 53, 04EE13.	1.5	5
98	A 0.5-V 5.8-GHz ultra-low-power RF transceiver for wireless sensor network in 65nm CMOS., 2014,,.		5
99	A sub-1G CMOS-MEMS accelerometer. , 2015, , .		5
100	Enhancement in structure stability of gold micro-cantilever by constrained fixed-end in MEMS devices. Microelectronic Engineering, 2018, 187-188, 105-109.	2.4	5
101	Sample geometry effect on mechanical property of gold micro-cantilevers by micro-bending test. MRS Communications, 2020, 10, 434-438.	1.8	5
102	Development of Scanning Âμ-RHEED Microscopy for Imaging Polycrystal Grain Structure in LSI. Japanese Journal of Applied Physics, 1989, 28, 2075-2077.	1.5	5
103	Variable RF Inductor on Si CMOS Chip. , 2003, , .		5
104	Reconfigurable RF CMOS Circuit for Cognitive Radio. IEICE Transactions on Communications, 2008, E91-B, 10-13.	0.7	5
105	Evaluation of LaB6Thin Film as Low-Work-Function Gate for MOSFET Operated at Low Temperature. Japanese Journal of Applied Physics, 1990, 29, L1594-L1596.	1.5	4
106	Novel Low-Power Switched-Current Matched Filter for Direct-Sequence Code-Division-Multiple-Access Wireless Communication. Japanese Journal of Applied Physics, 2000, 39, 2301-2304.	1.5	4
107	Derivation of interconnect length distribution in X architecture LSIs., 0, , .		4
108	A 8-Gbps Low-Latency Multi-Drop On-Chip Transmission Line Interconnect with 1.2-mW Two-Way Transceivers. , 2007, , .		4

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109	An 8Gbps 2.5mW on-chip pulsed-current-mode transmission line interconnect with a stacked-switch Tx., 2008, , .		4
110	A MOS transistor array with pico-ampere order precision for accurate characterization of leakage current variation. , $2008$ , , .		4
111	A Study of Digitally Controllable Radio Frequency Micro Electro Mechanical Systems Inductor. Japanese Journal of Applied Physics, 2011, 50, 05EE01.	1.5	4
112	Planar Solenoidal Inductor in Radio Frequency Micro-Electro-Mechanical Systems Technology for Variable Inductor with Wide Tunable Range and High Quality Factor. Japanese Journal of Applied Physics, 2012, 51, 05EE02.	1.5	4
113	A 0.5-V 2.5-GHz high-gain low-power regenerative amplifier based on Colpitts oscillator topology in 65-nm CMOS. , $2014,  \ldots$		4
114	An RF energy harvesting power management circuit for appropriate duty-cycled operation. Japanese Journal of Applied Physics, 2015, 54, 04DE11.	1.5	4
115	0.5 V 5.8 GHz highly linear current-reuse voltage-controlled oscillator with back-gate tuning technique. Japanese Journal of Applied Physics, 2015, 54, 04DE06.	1.5	4
116	E-band filters based on substrate integrated waveguide octagonal cavities loaded by complementary split-ring resonators. , 2015, , .		4
117	Deformation behavior of electroplated gold composed of nano-columnar grains embedded in micro-columnar textures. Materials Letters, 2017, 202, 82-85.	2.6	4
118	Particle Counting in Semiconductor Processing Gas and Apparatus with a New Flow-Cell-Type Laser Particle Counter. Japanese Journal of Applied Physics, 1990, 29, L2405-L2407.	1.5	3
119	In-SituCounting of Process-Induced Particles. Japanese Journal of Applied Physics, 1992, 31, 918-920.	1.5	3
120	Short-channel-effect free 0.18 /spl mu/m MOSFET by temperature-dimension combination scaling theory: design and experiment. IEEE Electron Device Letters, 1994, 15, 202-205.	3.9	3
121	ULSI interconnect length distribution model considering core utilization. , 0, , .		3
122	Differential transmission line structure for over 10 Gbps signal transmission at global interconnect in Si ULSI. , 0, , .		3
123	On-chip high-Q solenoid inductors embedded in WL-CSP. , 0, , .		3
124	Small-Area Inductor for Silicon CMOS Chips. Japanese Journal of Applied Physics, 2005, 44, 2766-2769.	1.5	3
125	Evaluation of on-chip transmission line interconnect using wire length distribution. , 2005, , .		3
126	Twisted Differential Transmission Line Structure for Global Interconnect in Si LSI. Japanese Journal of Applied Physics, 2005, 44, 2774-2779.	1.5	3

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127	A Loss Optimization Method Using WD Product for On-Chip Differential Transmission Line Design. , 2006, , .		3
128	A Low-Power Low-Phase-Noise CMOS VCO using RF SiP Technology. , 2007, , .		3
129	A Wideband CMOS LC-VCO Using Variable Inductor. , 2007, , .		3
130	On-chip differential and common mode voltage measurement using off-chip referenced twin probing. , 2008, , .		3
131	Accurate parasitic inductance determination of a ceramic capacitor through 2-port measurements. , 2008, , .		3
132	A low phase noise LC-VCO with a high-Q inductor fabricated by wafer level package technology. , 2008, , .		3
133	Substrate-geometry aware 2-port modeling for surface-mount passive components. , 2008, , .		3
134	A 21 V output charge pump circuit with appropriate well-bias supply technique in 0.18 $\pm$ x03BC;m Si CMOS. , 2011, , .		3
135	A dual-axis MEMS inertial sensor using multi-layered high-density metal for an arrayed CMOS-MEMS accelerometer. , 2014, , .		3
136	A design of spring constant arranged for MEMS accelerometer by multi-layer metal technology. , 2016,		3
137	A damping constant model for proof-mass structure design of MEMS inertial sensor by multi-layer metal technology. , 2016, , .		3
138	Evaluation and modeling of adhesion layer in shock-protection structure for MEMS accelerometer. Microelectronics Reliability, 2016, 66, 78-84.	1.7	3
139	Long-term structure stability of Ti/Au layered micro-cantilever evaluated by vibration test. Microelectronic Engineering, 2019, 207, 33-36.	2.4	3
140	Cu-alloying effect on structure stability of electrodeposited gold-based micro-cantilever evaluated by long-term vibration test. Microelectronic Engineering, 2019, 215, 111001.	2.4	3
141	Strengthening of micro-cantilever by Au/Ti bi-layered structure evaluated by micro-bending test toward MEMS devices. Microelectronic Engineering, 2019, 213, 13-17.	2.4	3
142	High-Sensitivity Inertial Sensor Module to Measure Hidden Micro Muscular Sounds. , 2019, , .		3
143	An Evaluation Method of Brownian Noise in Highly Sensitive Capacitive Sensors. IEEJ Transactions on Sensors and Micromachines, 2015, 135, 142-143.	0.1	3
144	A Study of Digitally Controllable Radio Frequency Micro Electro Mechanical Systems Inductor. Japanese Journal of Applied Physics, 2011, 50, 05EE01.	1.5	3

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145	Weakness Identification for Effective Repair of Power Distribution Network. Lecture Notes in Computer Science, 2007, , 222-231.	1.3	3
146	(GaAl)As/GaAs Solar Cells–Dopant Study of Zn and Be. Japanese Journal of Applied Physics, 1980, 19, 191.	1.5	2
147	Low-Temperature Metal-Oxide-Semiconductor Field-Effect Transistor Operation by Temperature Scaling Theory. Japanese Journal of Applied Physics, 1993, 32, 419-422.	1.5	2
148	High-Rate Deposition of High-Quality Silicon Nitride Film at Room Temperature by Quasi-Remote Plasma Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1995, 34, 6824-6826.	1.5	2
149	High speed and low power on-chip micro network circuit with differential transmission line. , 0, , .		2
150	Prediction of delay time for future LSI using on-chip transmission line interconnects., 2005,,.		2
151	Wire Length Distribution Model Considering Core Utilization for System on Chip., 0,,.		2
152	Zero-Crosstalk Bus Line Structure for Global Interconnects in Si Ultra Large Scale Integration. Japanese Journal of Applied Physics, 2006, 45, 4977-4981.	1.5	2
153	Adaptable wire-length distribution with tunable occupation probability. , 2007, , .		2
154	A Multi-Drop Transmission-Line Interconnect in Si LSI., 2007,,.		2
155	Small-Area CMOS RF Distributed Mixer Using Multi-Port Inductors. , 2007, , .		2
156	One-Chip Integration of Rapid Diagnosis Infectious-Disease Chip Based on New Phenomena of DNA Trap and Denature in Nanogaps. Japanese Journal of Applied Physics, 2008, 47, 3214-3219.	1.5	2
157	Linear Time Calculation of On-Chip Power Distribution Network Capacitance Considering State-Dependence. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2010, E93-A, 2409-2416.	0.3	2
158	Linear time calculation of state-dependent power distribution network capacitance., 2010,,.		2
159	High Strength Electrodeposited Au-Cu Alloys Evaluated by Bending Test toward Movable Micro-Components. ECS Journal of Solid State Science and Technology, 2019, 8, P412-P415.	1.8	2
160	Alloy Electroplating and Young's Modulus Characterization of AuCu Alloy Microcantilevers. Journal of the Electrochemical Society, 2020, 167, 082503.	2.9	2
161	Effective Young's Modulus of Complex Three Dimensional Multilayered Ti/Au Micro-Cantilevers Fabricated by Electrodeposition and the Temperature Dependency. Electrochem, 2021, 2, 216-223.	3.3	2
162	Wire Length Distribution Model for System LSI. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3445-3452.	0.3	2

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163	An Evaluation Method of the Number of Monte Carlo STA Trials for Statistical Path Delay Analysis. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2008, E91-A, 957-964.	0.3	2
164	Effect of current density on micro-mechanical property of electrodeposited gold film evaluated by micro-compression. Surface and Coatings Technology, 2022, 436, 128315.	4.8	2
165	Effects of Hydrogen Terminated Substrate Surface on Succeeding Selective Deposition. Materials Research Society Symposia Proceedings, 1993, 315, 59.	0.1	1
166	Multilevel metallization based on Al CVD., 0,,.		1
167	Self-Aligned 10-nm Barrier Layer Formation Technology for Fully Self-Aligned Metallization Metal-Oxide-Semiconductor Field-Effect-Transistor. Japanese Journal of Applied Physics, 1998, 37, 3264-3267.	1.5	1
168	Lower Boundary of Supply Voltage in Digital ULSI Based on the Communication Theory. Japanese Journal of Applied Physics, 2003, 42, L1133-L1135.	1.5	1
169	High speed and low power global interconnect IP with differential transmission line and driver-receiver circuits. , 0, , .		1
170	A Reconfigurable RF Circuit Architecture for Dynamic Power Reduction., 2005,,.		1
171	Improvement of Variable Ratio of On-Chip Variable Inductors Using Side Shield. Japanese Journal of Applied Physics, 2006, 45, 5720-5723.	1.5	1
172	$\label{thm:linear_connect} \mbox{High-Crosstalk Robustness Transmission Line Interconnect in Si LSI using Zero-Crosstalk Structure.} \ , \ 2006, , . \ .$		1
173	Improvement of power distribution network using correlation-based regression analysis., 2007,,.		1
174	Design of High-Density Interconnects for High-Speed Transmission. , 2007, , .		1
175	Determination of optimal polynomial regression function to decompose on-die systematic and random variations. , 2008, , .		1
176	Challenges in integration of diverse functionalities on CMOS. , 2013, , .		1
177	A Sub-1mW Class-C-VCO-Based Low Voltage PLL with Ultra-Low-Power Digitally-Calibrated ILFD in 65nm CMOS. IEICE Transactions on Electronics, 2014, E97.C, 495-504.	0.6	1
178	An ultra low power pH-monitoring IC with a duty-cycling wireless FM-transmitter. , 2014, , .		1
179	A 0.5-V 1.56-mW 5.5-GHz RF transceiver IC module with J-shaped folded monopole antenna. , 2015, , .		1
180	An ultra-low-power 32QAM RF transmitter. , 2015, , .		1

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181	Path Clustering for Test Pattern Reduction of Variation-Aware Adaptive Path Delay Testing. Journal of Electronic Testing: Theory and Applications (JETTA), 2016, 32, 601-609.	1.2	1
182	Development of high sensitivity CMOS-MEMS inertia sensor and its application to early-stage diagnosis of Parkinson's disease., 2016,,.		1
183	Design of high-frequency piezoelectric resonator-based cascaded fractional-N PLL with sub-ppb-order channel adjusting technique., 2017,,.		1
184	Fabrication of Au-Cu Alloy/Ti Layered Micro-Cantilevers and the Long-Term Structure Stability. , 2019, , .		1
185	Co-Electrodeposition of Au–TiO2 Nanocomposite and the Micro-Mechanical Properties. Electrochem, 2020, 1, 388-393.	3.3	1
186	Circuit Performance Prediction Considering Core Utilization with Interconnect Length Distribution Model. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3358-3366.	0.3	1
187	Application of Correlation-Based Regression Analysis for Improvement of Power Distribution Network. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2008, E91-A, 951-956.	0.3	1
188	Hypersphere Sampling for Accelerating High-Dimension and Low-Failure Probability Circuit-Yield Analysis. IEICE Transactions on Electronics, 2014, E97.C, 280-288.	0.6	1
189	Temperature scaling concept of MOSFET. European Physical Journal Special Topics, 1994, 04, C6-3-C6-12.	0.2	1
190	Crystallographic Structures and Parasitic Resistances of Self-Aligned Silicide TiSi2/Self-Aligned Nitrided Barrier Layer/Selective Chemical Vapor Deposited Aluminum in Fully Self-Aligned Metallization Metal Oxide Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 1999, 38, 5835-5838.	1.5	0
191	Near field communication chip using PIM for bio MEMS sensors. , 0, , .		0
192	A batteryless wireless communication circuit for measurement of gastric acid., 2006,,.		0
193	Estimation of Power Reduction by On-Chip Transmission Line for 45nm Technology. Lecture Notes in Computer Science, 2006, , 181-190.	1.3	O
194	Optimization Methodology of Layer Numbers with Circuit/Process Co-Design. Japanese Journal of Applied Physics, 2006, 45, 2476-2480.	1.5	0
195	On-Chip Yagi–Uda Antenna for Horizontal Wireless Signal Transmission in Stacked Multi Chip Packaging. Japanese Journal of Applied Physics, 2007, 46, 2283-2286.	1.5	O
196	A 5.2 GHz CMOS Low Noise Amplifier with High-Q Inductors Embedded in Wafer-Level Chip-Scale Package. , 2007, , .		0
197	Reconfigurable CMOS Low Noise Amplifier Using Variable Bias Circuit for Self Compensation., 2007,,.		0
198	LVDS-type on-chip transmision line interconnect with passive equalizers in 90nm CMOS process. , 2008, , .		0

#	Article	IF	CITATIONS
199	A Low-Power Differential Transmission Line Interconnect Using Wafer Level Package Technology. , 2008, , .		0
200	Non-invasive direct probing for on-chip voltage measurement. , 2008, , .		0
201	Inter-Chip Wiring Technology for 3-D LSI. Electrochemistry, 2009, 77, 812-817.	1.4	O
202	A Universal Equivalent Circuit Model for Ceramic Capacitors. IEICE Transactions on Electronics, 2010, E93-C, 347-354.	0.6	0
203	Scan based process parameter estimation through path-delay inequalities. , 2010, , .		O
204	Decomposition of drain-current variation into gain-factor and threshold voltage variations. , 2010, , .		0
205	Interconnect Design Challenges in Nano CMOS Circuit. Key Engineering Materials, 0, 470, 224-230.	0.4	O
206	A 1mG-to-20G integrated MEMS inertial sensor. , 2014, , .		0
207	A 0.5-V 5.8-GHz low-power asymmetrical QPSK/OOK transceiver for wireless sensor network., 2015,,.		O
208	Development of high sensitivity CMOS-MEMS inertia sensor and its application to early-stage diagnosis of Parkinson's disease., 2016,,.		0
209	A MEMS ACCELEROMETER WITH A SINGLE AXIS TWO PROOF MASSES FOR A WIDE DETECTION RANGE. , 2021, , .		0
210	Evaluation of X Architecture Using Interconnect Length Distribution. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3437-3444.	0.3	0
211	Statistical Modeling of a Via Distribution for Yield Estimation. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2006, E89-A, 3579-3584.	0.3	0
212	Low-Loss Distributed Constant Passive Devices Using Wafer-Level Chip Scale Package Technology. IEICE Transactions on Electronics, 2007, E90-C, 641-643.	0.6	0
213	Tunable CMOS LNA Using a Variable Inductor for a Reconfigurable RF Circuit. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 401-410.	0.3	0
214	Analytical Estimation of Path-Delay Variation for Multi-Threshold CMOS Circuits. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 1031-1038.	0.3	0
215	One-Shot Voltage-Measurement Circuit Utilizing Process Variation. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 1024-1030.	0.3	0
216	2-Port Modeling Technique for Surface-Mount Passive Components Using Partial Inductance Concept. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 976-982.	0.3	0

#	Article	IF	CITATIONS
217	A Time-Slicing Ring Oscillator for Capturing Time-Dependent Delay Degradation and Power Supply Voltage Fluctuation. IEICE Transactions on Electronics, 2010, E93-C, 324-331.	0.6	O
218	State-Dependence of On-Chip Power Distribution Network Capacitance. IEICE Transactions on Electronics, 2014, E97.C, 77-84.	0.6	0
219	(Invited) CMOS-MEMS Based Microgravity Sensor and Its Application. ECS Meeting Abstracts, 2020, MA2020-01, 1375-1375.	0.0	O
220	Effects of Sample Geometry on Micro-Mechanical Property of Single Crystal Gold for Applications in Microelectronics. ECS Meeting Abstracts, 2020, MA2020-02, 3307-3307.	0.0	0
221	A Simplified Analytical Damping Constant Model for Perforated Proof Mass Structure of MEMS Capacitive Accelerometer by Multi-Layer Metal Technology. , 2021, , .		0